

Rev.2.5 Aug. 5 2022

JSKT090/JSKH090

Description

- 1) A package of series of two chips.
- 2) With high thermal conductivity DBC as the insulation.
- 3) Welding by vacuum welding technology, which provide high reliability.

Typical Application

DC motor control, temperature control and light control system.



Absolute Maximum Ratings (Packaged into modules, unless otherwise specified, T_{CASE}=25°C)

Parameter	Test Conditions	Symbol	Values			
			12	16	18	Unit
Operating junction temperature range		Tj	-40-125			°C
Storage temperature range		T _{stg}	-40-125			°C
Repetitive peak off-state voltage	T j =25 ℃	V _{DRM}	1200	1600	1800	V
Repetitive peak reverse voltage	Tj =25 ℃	V _{RRM}	1200	1600	1800	V
Non-repetitive peak off-state voltage	T j =25 ℃	V _{DSM}	1300	1700	1900	V
Non-repetitive peak reverse voltage	T j =25 ℃	V _{RSM}	1300	1700	1900	V
Average on-state current	Tc=85℃	I _{T(AV)} /I _{F(AV)}	90		А	
Peak on-state surge current	t _P =10ms V _R =0.6V _{RRM}	I _{TSM} /I _{FSM}	1800		A	
l ² t value for fusing	t _P =10ms V _R =0.6V _{RRM}	l ² t	16200		A ² s	
Critical rate of rise of on-state current	I _G =2×I _{GT}	dl/dt	150		A/µs	
Insulation voltage	A.C 50Hz(1s/1min)	V _{ISO}	3600/3000			V

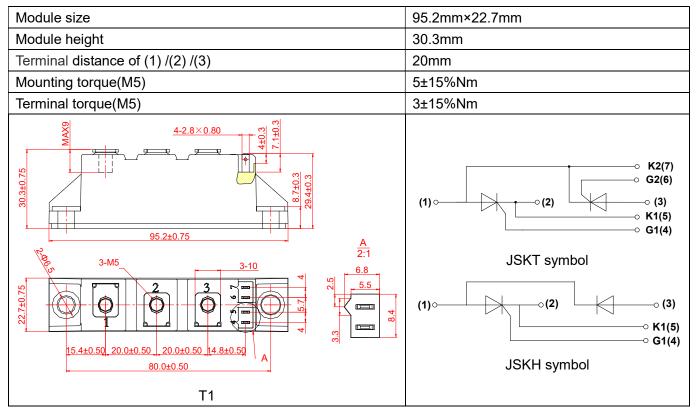
Electrical Characteristics (Packaged into modules, unless otherwise specified, T_{CASE}=25°C)

Parameter	Test Conditions	Symbol	Values	Unit
Peak on-state voltage	I _T =270A t _P =380µs	V _{TM}	≤1.8	V
Threshold voltage	Tj=125℃	V _{TO}	≤0.95	V
Dynamic resistance	Tj=125℃	R _d	≤2.1	mΩ
Repetitive peak off-state current	VD=VDRM Tc=25°С	I _{DRM1}	≤100	μA
	Tc=125℃	I _{DRM2}	≤30	mA



		1		
	Vr=Vrrm			
Repetitive peak reverse current	Tc=25℃	I _{RRM1}	≤100	μA
	Tc=125℃	I _{RRM2}	≤30	mA
Triggering gate current	$V_D=12V R_L=30\Omega$	I _{GT}	20-120	mA
Holding current	I _T =1A	I _H	≤250	mA
Latching current	Ig=1.2IgT	١L	≤300	mA
Triggering gate voltage	$V_D=12V R_L=30\Omega$	V _{GT}	≤1.8	V
Non triggering gate voltage	V _D =V _{DRM} T _j =125℃	V_{GD}	≥0.25	V
Critical rate of rise of voltage	V _D =2/3V _{DRM} Tj=125℃ Gate Open	dV/dt	≥1000	V/µs
Thermal resistance	Junction to base plate	R _{th(j-b)}	0.34	
	Case to heatsink	R _{th(c-s)}	0.22	°C/W
	Junction to case	R _{th(j-c)}	0.3	

Mechanical Characteristics





Instructions and Precautions

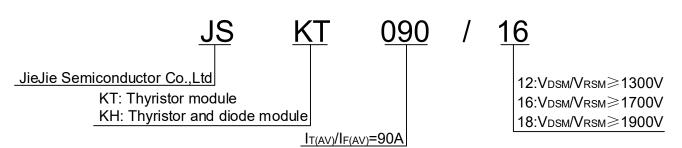
1) There is no severe vibration and shock in operating environment, and there should be no impurity and atmosphere which may corrode metal and damage the insulation in the air-dielectric.

2) The operating condition of the product can't out of range of the above parameters.

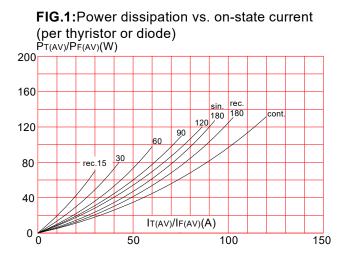
3) When the product is installed on the radiator, the radiator's surface should be confirmed flat, smooth, wipe clean with alcohol, and coated evenly with a layer of thermal grease which thickness is moderate on the contact surface between product and radiator. When the module is fastened on the surface of the radiator, the M5 or M6 screws and spring washers are used and fastened with 5NM torque. After the module is operated 1 hour, all screws must be refastened.

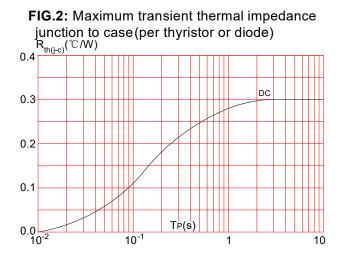
4) The connection with the main electrode of module can use copper, welding, socket and so on. The contact surface should be smooth and flat, which make good contact. While the connection with the control electrode of module is installed, attention should be paid to the corresponding connection of each pin. After the completion of the connection, do not plug and pull out the lead of the control electrode freely.

Ordering Information



Performance Curves







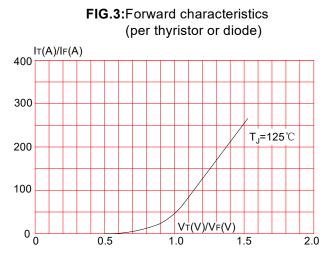
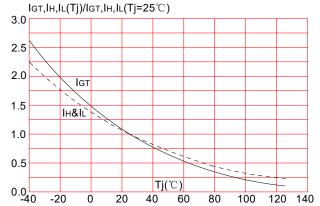


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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